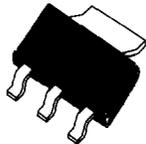


CZTA14 NPN  
CZTA64 PNP

SILICON COMPLEMENTARY  
DARLINGTON TRANSISTORS



SOT-23 CASE

**Central**<sup>TM</sup>  
**Semiconductor Corp.**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CZTA14, CZTA64 types are complementary silicon Darlington transistors manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for applications requiring extremely high gain.

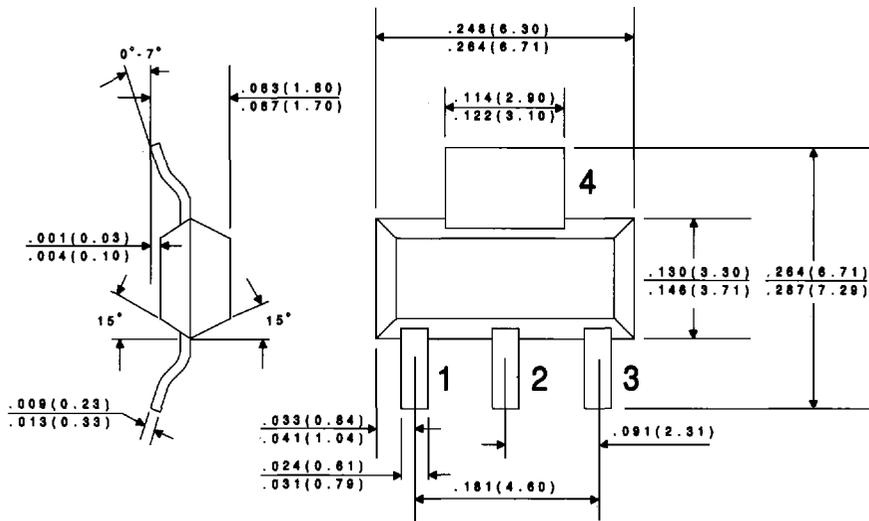
**MAXIMUM RATINGS** ( $T_A=25^{\circ}\text{C}$ )

	SYMBOL		UNITS
Collector-Base Voltage	$V_{CB0}$	30	V
Collector-Emitter Voltage	$V_{CE0}$	30	V
Emitter-Base Voltage	$V_{EB0}$	10	V
Collector Current	$I_C$	1,000	mA
Power Dissipation	$P_D$	2.0	W
Operating and Storage			
Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	$\Theta_{JA}$	62.5	$^{\circ}\text{C/W}$

**ELECTRICAL CHARACTERISTICS** ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$I_{CBO}$	$V_{CB}=30\text{V}$		100	nA
$I_{CEO}$	$V_{CE}=10\text{V}$		100	nA
$BV_{CES}$	$I_C=100\mu\text{A}$	30		V
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=0.1\text{mA}$		1.5	V
$V_{BE(ON)}$	$V_{CE}=5.0\text{V}, I_C=100\text{mA}$		2.0	V
$h_{FE}$	$V_{CE}=5.0\text{V}, I_C=10\text{mA}$	10,000		
$h_{FE}$	$V_{CE}=5.0\text{V}, I_C=100\text{mA}$	20,000		
$f_T$	$V_{CE}=5.0\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	125		MHz

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR

DATA SHEET

R2